

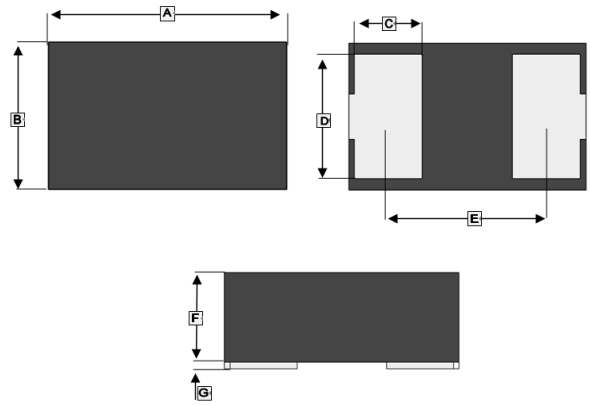
RoHS Compliant Product  
A suffix of "-C" specifies halogen and lead-free

**DESCRIPTION**

SBESD5411N is a bi-directional Transient Voltage Suppressor (TVS). It is specifically designed to protect sensitive electronic components which are connected to low speed data lines and control lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and lightning.

SBESD5411N may be used to provide ESD protection up to  $\pm 30\text{kV}$  (contact and air discharge) according to IEC 61000-4-2 and withstand peak pulse current up to 6A (8/20 $\mu\text{s}$ ) according to IEC 61000-4-5.

**DFN1006-2L**



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.95	1.05	E	0.65 TYP.	
B	0.55	0.65	F	0.3	0.4
C	0.2	0.3	G	0.00	0.05
D	0.45	0.55			

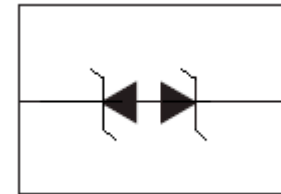
**FEATURES**

- Low clamping voltage
- Ultra-low leakage current
- Solid-state silicon technology

**APPLICATIONS**

- Tablets
- Laptops
- Other portable devices

**MARKING**



**PACKAGE INFORMATION**

Package	MPQ	Leader Size
DFN1006-2L	10K	7 inch

**ABSOLUTE MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Rating		Symbol	Value	Unit
IEC 61000-4-2	Air discharge	$V_{ESD}$	$\pm 30$	kV
	Contact discharge		$\pm 30$	
Peak Pulse Power@ $t_p=8/20\mu\text{s}$		$P_{PK}$	70	W
Peak Pulse Current@ $t_p=8/20\mu\text{s}$		$I_{PP}$	6	A
Operating Temperature		$T_{OP}$	-40~85	$^\circ\text{C}$
Lead Temperature		$T_L$	260	$^\circ\text{C}$
Junction and Storage Temperature Range		$T_J, T_{STG}$	125, -55~150	$^\circ\text{C}$

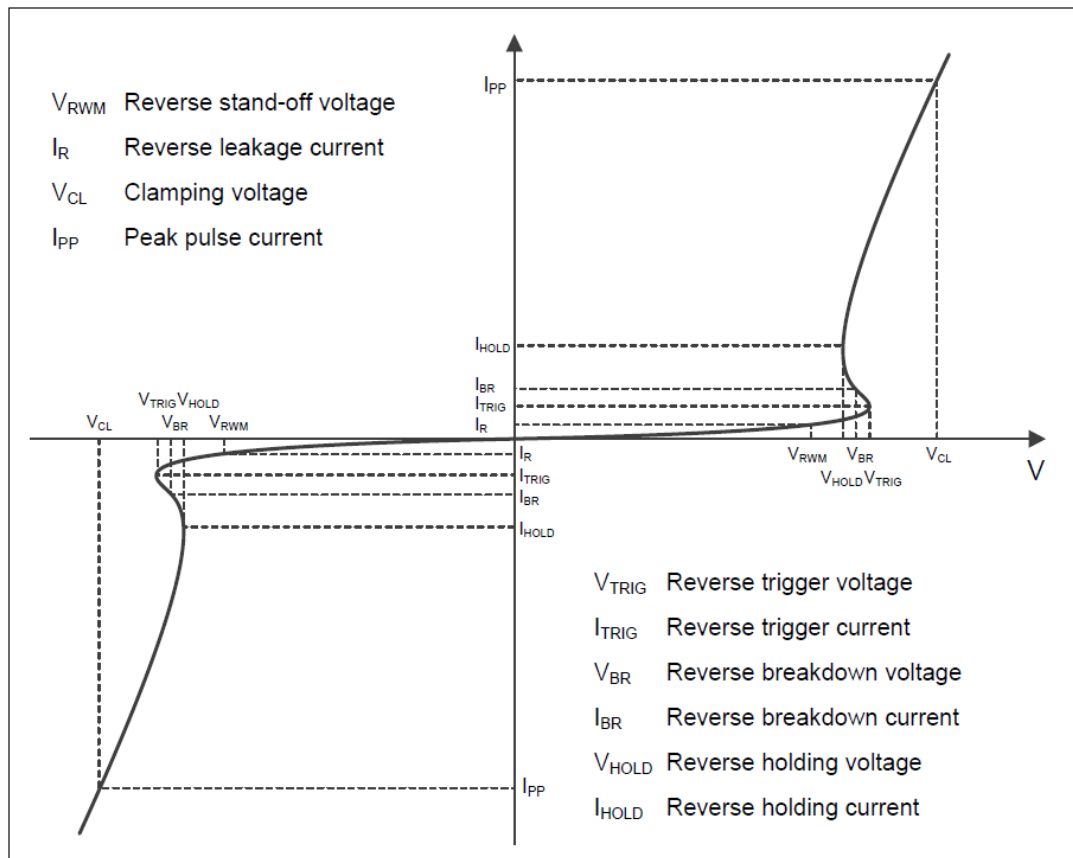
**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Maximum Reverse Working Voltage	$V_{RWM}$		-	-	7	V
Reverse Leakage Current	$I_R$	$V_{RWM}=7\text{V}$	-	5	100	nA
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1\text{mA}$	7.2	-	10.5	V
Reverse Holding Voltage	$V_{HOLD}$	$I_{HOLD}=50\text{mA}$	7.2	-	10.5	V
Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP}=16\text{A}$ , $t_p=100\text{ns}$	-	12	-	V
Clamping Voltage <sup>2</sup>	$V_C$	$V_{ESD}=8\text{kV}$	-	12	-	V
Clamping Voltage <sup>3</sup>	$V_C$	$I_{PP}=1\text{A}$ , $t_p=8/20\mu\text{s}$	-	-	10	V
		$I_{PP}=6\text{A}$ , $t_p=8/20\mu\text{s}$	-	-	12	V
Dynamic Resistance	$R_{DYN}$		-	0.24	-	$\Omega$
Junction Capacitance	$C_J$	$V_R=0$ , $f=1\text{MHz}$	-	17.5	22	pF
		$V_R=7\text{V}$ , $f=1\text{MHz}$	-	11.5	16	

Notes:

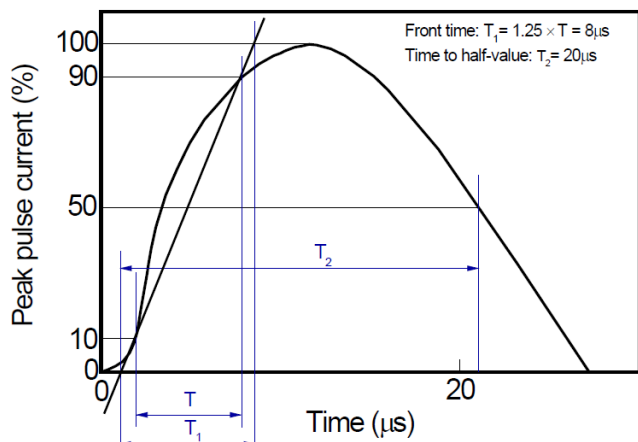
1. TLP parameters:  $Z_0=50\Omega$ ,  $t_p=100\text{ns}$ ,  $t_r=2\text{ns}$ , average window moves from 60ns to 80ns.  $R_{DYN}$  is calculated from 10A to 30A.
2. According to IEC61000-4-2, contact discharge mode.
3. According to IEC61000-4-5, non-repetitive pulse current.

**CHARACTERISTICS CURVES** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

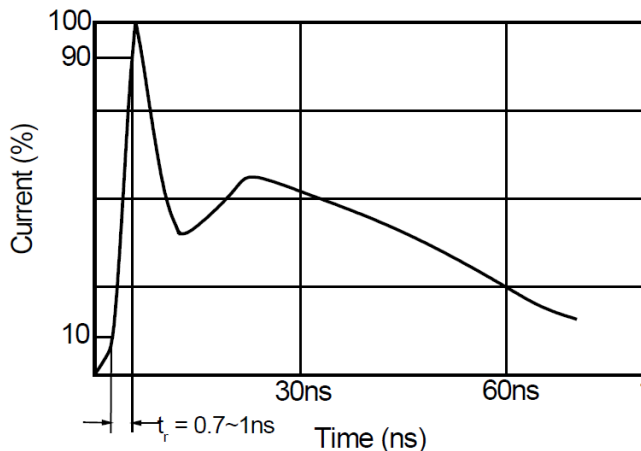


Definitions of electrical characteristics

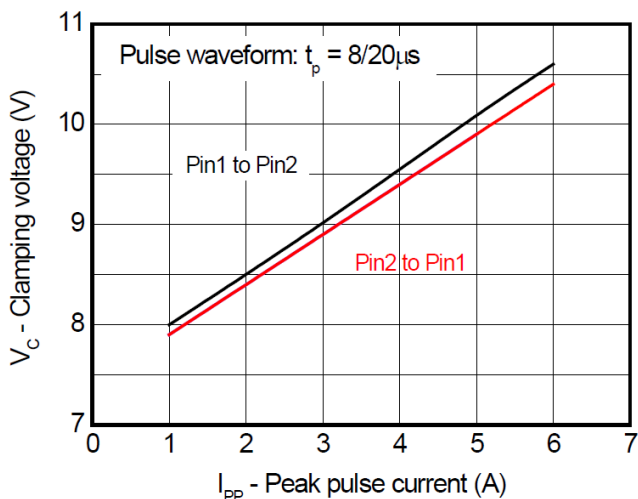
**CHARACTERISTICS CURVES**



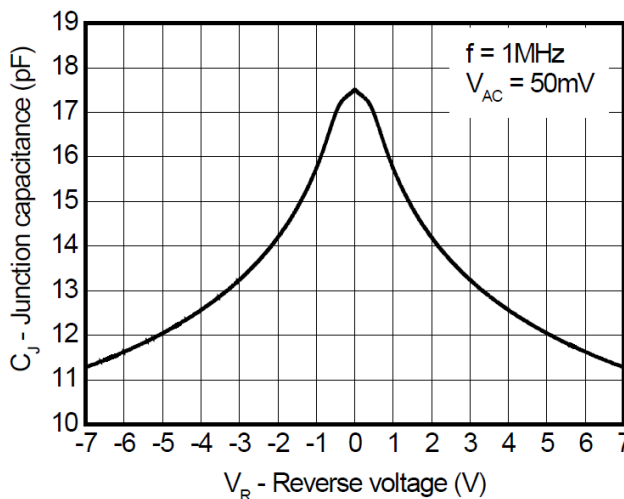
8/20µs waveform per IEC61000-4-5



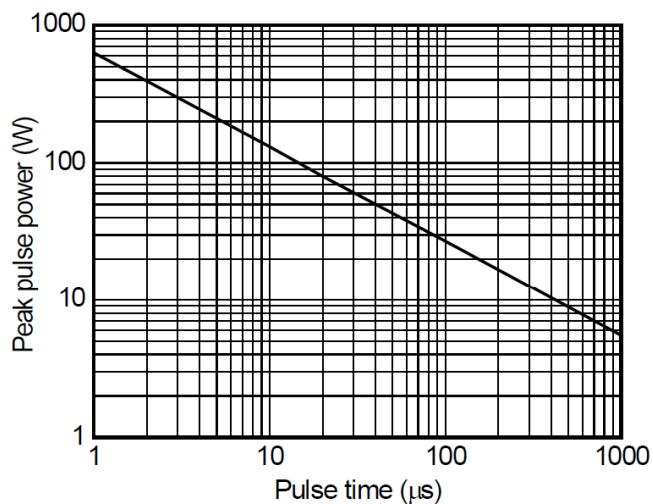
Contact discharge current waveform per IEC61000-4-2



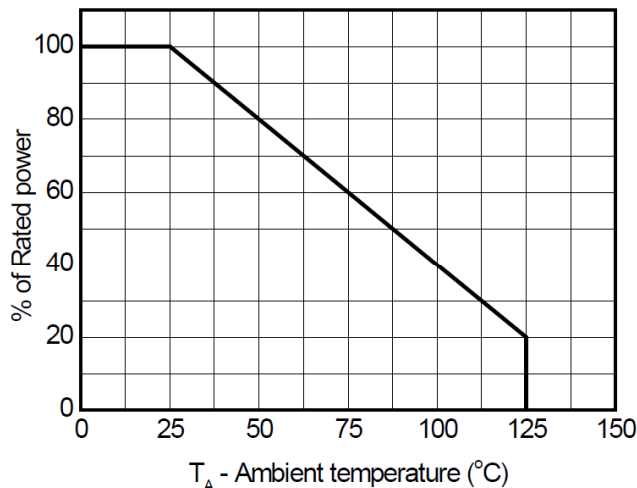
Clamping voltage vs. Peak pulse current



Capacitance vs. Reverse voltage

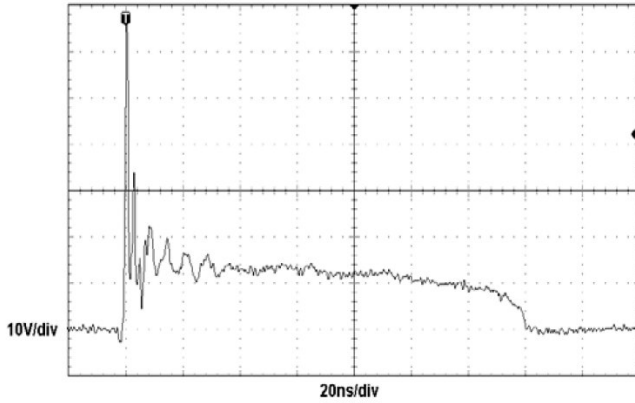


Non-repetitive peak pulse power vs. Pulse time

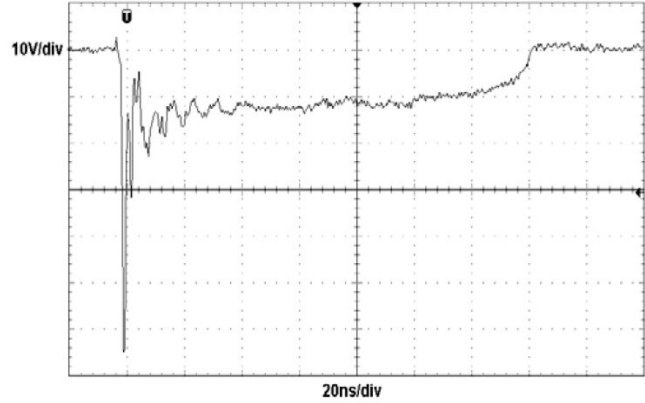


Power derating vs. Ambient temperature

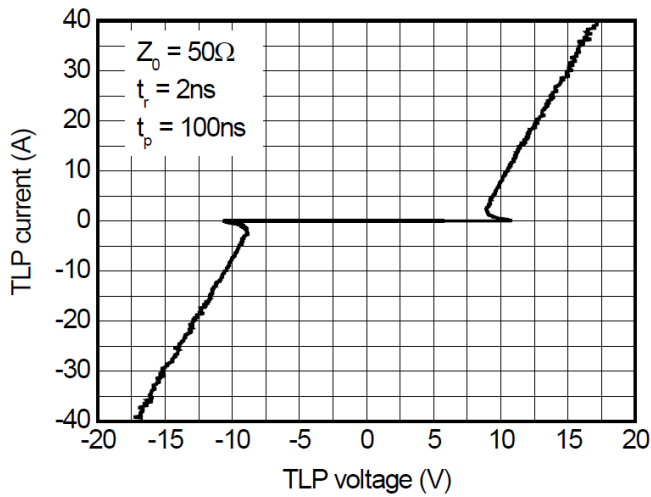
**CHARACTERISTICS CURVES**



**ESD clamping**  
(+8kV contact discharge per IEC61000-4-2)



**ESD clamping**  
(-8kV contact discharge per IEC61000-4-2)



**TLP Measurement**